Unit: mm

TOSHIBA Transistor Silicon PNP / NPN Epitaxial Type (PCT Process)

# **HN4B102J**

# MOS Gate Drive Applications Switching Applications

• Small footprint due to a small and thin package

• High DC current gain : PNP  $h_{FE}$  = 200 to 500 ( $I_{C}$  = -0.2 A)

: NPN  $h_{FE} = 200 \text{ to } 500 \text{ (I}_{C} = 0.2 \text{ A)}$ 

• Low collector-emitter saturation : PNP V<sub>CE (sat)</sub> =−0.20 V (max)

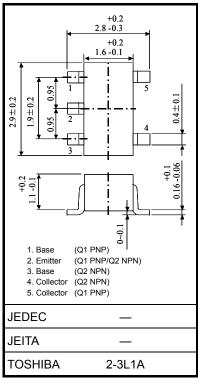
: NPN  $V_{CE (sat)} = 0.14 \text{ V (max)}$ 

• High-speed switching : PNP  $t_f = 40 \text{ ns (typ.)}$ 

: NPN  $t_f = 45 \text{ ns (typ.)}$ 

### Absolute Maximum Ratings (Ta = 25°C)

| Characteristic                         |                         | Cumbal                  | Rating     |      | Unit |  |
|--|-------------------------|-------------------------|------------|------|------|--|
| Character                              | Symbol                  | PNP                     | NPN        | Oill |      |  |
| Collector-base voltage                 | $V_{CBO}$               | -30                     | 60         | V    |      |  |
| Collector-emitter volta                | $V_{CEO}$               | -30                     | 30         | V    |      |  |
| Emitter-base voltage                   | $V_{EBO}$               | -7                      | 7          | V    |      |  |
| Collector current                      | DC (Note 1)             | Ic                      | -1.8       | 2.0  | Α    |  |
| Collector current                      | Pulse (Note 1)          | I <sub>CP</sub>         | -8.0       | 8.0  | ζ    |  |
| Base current                           | $I_{B}$                 | -0.5                    | 0.5        | Α    |      |  |
| Collector power dissipation (t = 10 s) | Single-device operation | P <sub>C</sub> (Note 2) | 1.1        |      | W    |  |
| Collector power dissipation (DC)       | Single-device operation | P <sub>C</sub> (Note 2) | 0.75       |      | W    |  |
| Junction temperature                   | Tj                      | 150                     |            | °C   |      |  |
| Storage temperature range              |                         | T <sub>stg</sub>        | -55 to 150 |      | °C   |  |



Weight: 0.014g (typ.)

- Note 1: Ensure that the channel temperature does not exceed 150°C during use of the device.
- Note 2: Mounted on an FR4 board (glass-epoxy; 1.6 mm thick; Cu area, 645 mm<sup>2</sup>)

Note 3: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Figure 1 Circuit Configuration (top view)

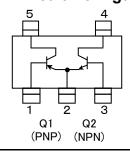
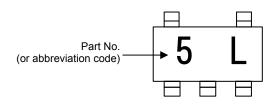


Figure 2 Marking



## **Electrical Characteristics (Ta = 25°C)**

#### **PNP**

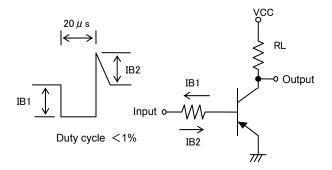
| Char                                 | racteristic  | Symbol                | Test Condition  | Min | Тур. | Max   | Unit |
|--------------------------------------|--------------|-----------------------|---|-----|------|-------|------|
| Collector cut-off current            |              | I <sub>CBO</sub>      | $V_{CB} = -30 \text{ V}, I_E = 0$   | _   | _    | -100  | nA   |
| Emitter cut-off current              |              | I <sub>EBO</sub>      | $V_{EB} = -7 \text{ V}, I_{C} = 0$  | _   | _    | -100  | nA   |
| Collector-emitter breakdown voltage  |              | V (BR) CEO            | $I_C = -10 \text{ mA}, I_B = 0$   | -30 | _    | _     | V    |
| DC current gain                      |              | h <sub>FE</sub> (1)   | $V_{CE} = -2 \text{ V}, I_{C} = -0.2 \text{ A}$   | 200 | _    | 500   |      |
|                                      |              | h <sub>FE</sub> (2)   | $V_{CE} = -2 \text{ V}, I_{C} = -0.6 \text{ A}$   | 125 | _    | _     |      |
|                                      |              | h <sub>FE</sub> (3)   | $V_{CE} = -2 \text{ V}, I_{C} = -2.0 \text{ A}$   | 40  | _    | _     |      |
| Collector-emitter saturation voltage |              | V <sub>CE</sub> (sat) | $I_C = -0.6 \text{ A}, I_B = -20 \text{ mA}$  | _   | _    | -0.20 | V    |
| Base-emitter saturation voltage      |              | V <sub>BE</sub> (sat) | $I_C = -0.6 \text{ A}, I_B = -20 \text{ mA}$  | _   | _    | -1.10 | V    |
| Collector output capacitance         |              | C <sub>ob</sub>       | V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1MHz   | _   | 16.5 | _     | pF   |
| Switching time                       | Rise time    | t <sub>r</sub>        | See Figure 3 circuit diagram V <sub>CC</sub> i≒−18 V, R <sub>L</sub> = 30 Ω I <sub>B1</sub> = I <sub>B2</sub> = 20 mA | _   | 40   | _     |      |
|                                      | Storage time | t <sub>stg</sub>      |   | _   | 280  | _     | ns   |
|                                      | Fall time    | t <sub>f</sub>        |   | _   | 40   | _     |      |

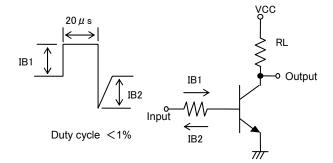
#### NPN

| Char                                 | acteristic   | Symbol                | Test Condition  | Min | Тур. | Max  | Unit |
|--------------------------------------|--------------|-----------------------|---|-----|------|------|------|
| Collector cut-off current            |              | I <sub>CBO</sub>      | V <sub>CB</sub> = 60 V, I <sub>E</sub> = 0  | _   | _    | 100  | nA   |
| Emitter cut-off current              |              | I <sub>EBO</sub>      | V <sub>EB</sub> = 7 V, I <sub>C</sub> = 0   | _   | _    | 100  | nA   |
| Collector-emitter breakdown voltage  |              | V (BR) CEO            | $I_C = 10 \text{ mA}, I_B = 0$  | 30  | _    | _    | V    |
| DC current gain                      |              | h <sub>FE</sub> (1)   | V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.2 A   | 200 | _    | 500  |      |
|                                      |              | h <sub>FE</sub> (2)   | V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.6 A   | 125 | _    | _    |      |
|                                      |              | h <sub>FE</sub> (3)   | V <sub>CE</sub> = 2 V, I <sub>C</sub> = 2.0 A   | 40  | _    | _    |      |
| Collector-emitter saturation voltage |              | V <sub>CE</sub> (sat) | I <sub>C</sub> = 0.6 A, I <sub>B</sub> = 20 mA  | _   | _    | 0.14 | V    |
| Base-emitter saturation voltage      |              | V <sub>BE</sub> (sat) | I <sub>C</sub> = 0.6 A, I <sub>B</sub> = 20 mA  | _   | _    | 1.10 | V    |
| Collector output capacitance         |              | C <sub>ob</sub>       | V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1MHz  | _   | 14   | _    | pF   |
| Switching time                       | Rise time    | t <sub>r</sub>        | See Figure 4 circuit diagram V <sub>CC</sub> ≒18 V, R <sub>L</sub> = 30 Ω I <sub>B1</sub> = I <sub>B2</sub> = 20 mA | _   | 45   | _    |      |
|                                      | Storage time | t <sub>stg</sub>      |   | _   | 580  | _    | ns   |
|                                      | Fall time    | t <sub>f</sub>        |   | _   | 45   | _    |      |

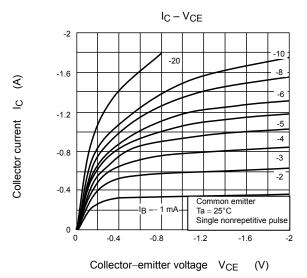
Figure 3. Switching Time Test Circuit & Timing Chart

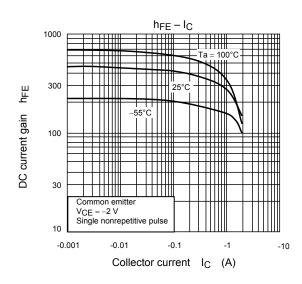
Figure 4. Switching Time Test Circuit & Timing Chart

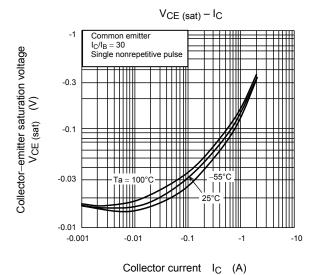


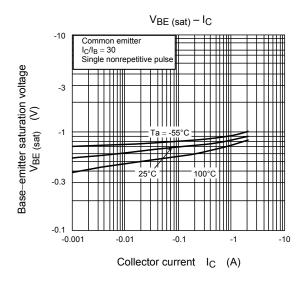


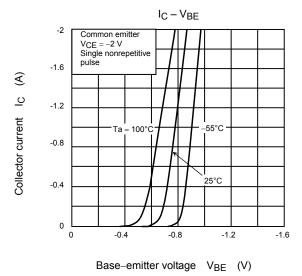
#### **PNP**

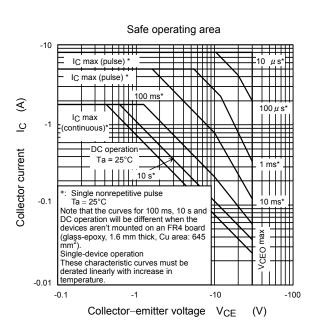




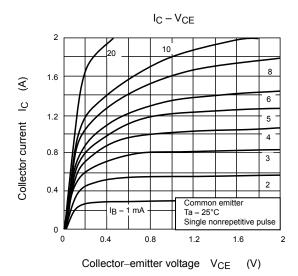


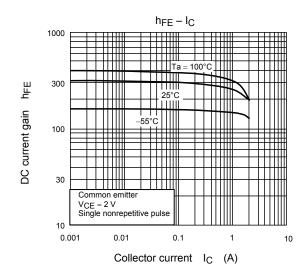


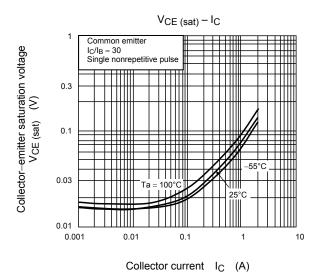


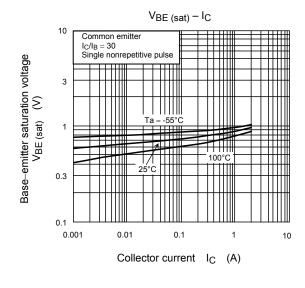


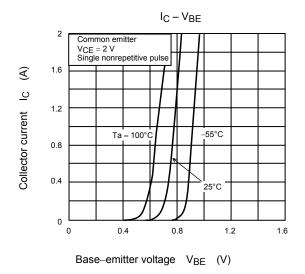
#### **NPN**

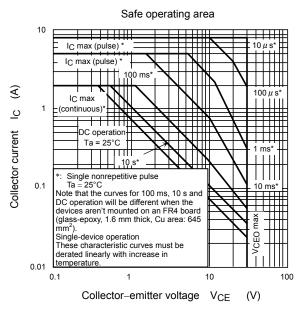




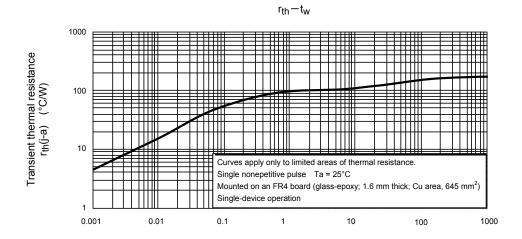








#### Common



Pulse width  $t_W$  (s)

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6